

ABSTRACT

A method for reading non-volatile memory arranged in columns and rows which reduces adjacent cell coupling, sometimes referred to as the Yupin effect. The method includes the steps of: selecting a bit to be read in a word-line; reading an adjacent word line written after word line; and reading the selected bit in word line by selectively adjusting at least one read parameter. In one embodiment, the read parameter is the sense voltage. In another embodiment, the read parameter is the pre-charge voltage. In yet another embodiment, both the sense and the pre-charge voltage are adjusted.